

### SINGLE 2 INPUT POSITIVE NAND GATE

#### Description

The 74LVCE1G00 is a single 2-input positive NAND gate with a standard totem pole output. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

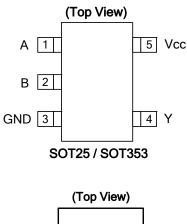
The gate performs the positive Boolean function:

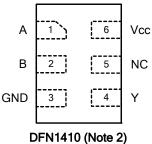
## $Y = \overline{A \bullet B} \text{ or } Y = \overline{A} + \overline{B}$

#### Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
  Exceeds 200-V Machine Model (A115-A)
  Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25, SOT353, and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

### Pin Assignments





#### Applications

- Voltage Level Shifting
- General Purpose Logic
- Wide array of products such as.
  - PCs, networking, notebooks, netbooks, PDAs
  - o Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders
- Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.
  - 2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

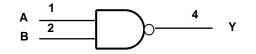


## SINGLE 2 INPUT POSITIVE NAND GATE

## **Pin Descriptions**

Pin Name	Description			
А	Data Input			
В	Data Input			
GND	Ground			
Y	Data Output			
Vcc	Supply Voltage			

# Logic Diagram



## **Function Table**

Inp	Output	
Α	В	Y
Н	Н	L
L	Х	Н
Х	L	Н



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### Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0	-50	mA
Ι <sub>οκ</sub>	Output Clamp Current	-50	mA
Ι <sub>Ο</sub>	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

74LVCE1G00 Document number: DS32210 Rev. 2 - 2



# SINGLE 2 INPUT POSITIVE NAND GATE

# **Recommended Operating Conditions (Note 4)**

Symbol		Parameter	Min	Max	Unit	
V		Operating	1.4	5.5	V	
V <sub>CC</sub>	Operating Voltage	Data retention only	1.2		V	
		$V_{\rm CC} = 1.4 \text{ V} \text{ to } 1.95 \text{ V}$	0.65 X V <sub>CC</sub>			
N/	Link laurel langet \/alta aa	$V_{\rm CC}$ = 2.3 V to 2.7 V	1.7			
V <sub>IH</sub>	High-level Input Voltage	$V_{CC} = 3 V$ to 3.6 V	2		V	
		$V_{\rm CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 X V <sub>CC</sub>			
		$V_{\rm CC} = 1.4 \text{ V}$ to 1.95 V		0.35 X V <sub>CC</sub>		
V		$V_{\rm CC}$ = 2.3 V to 2.7 V		0.7	V	
V <sub>IL</sub> Low-level input vol	Low-level input voltage	$V_{CC} = 3 V$ to 3.6 V		0.8	V	
		$V_{\rm CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.3 X V <sub>CC</sub>		
VI	Input Voltage	•	0	5.5	V	
Vo	Output Voltage		0	V <sub>cc</sub>	V	
	High-level output current	Vcc=1.4 V		-3		
		V <sub>CC</sub> = 1.65 V		-4		
		V <sub>CC</sub> = 2.3 V		-8		
I <sub>OH</sub>				-16	mA	
		$V_{CC} = 3 V$		-24		
		$V_{CC} = 4.5 V$		-32		
		Vcc=1.4 V		3		
		V <sub>CC</sub> = 1.65 V		4		
		$V_{CC} = 2.3 V$		8	mA	
I <sub>OL</sub>	Low-level output current			16		
		$V_{CC} = 3 V$		24		
		V <sub>CC</sub> = 4.5 V		32		
		$V_{\rm CC} = 1.4$ to 3V		20		
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
	rate	$V_{CC} = 5 V \pm 0.5 V$		5		
T <sub>A</sub>	Operating free-air temperature		-40	85	٥C	

Note: 4. Unused inputs should be held at Vcc or Ground.



## SINGLE 2 INPUT POSITIVE NAND GATE

### Electrical Characteristics (All typical values are at Vcc = 3.3V, T<sub>A</sub> = 25°C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit	
		I <sub>OH</sub> = -100µА	1.4 V to 5.5V	$V_{CC} - 0.1$				
		I <sub>OH</sub> = -3mA	1.4 V	1.05				
		I <sub>ОН</sub> = -4mA	1.65 V	1.2				
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -8mA	2.3V	1.9			V	
	vollage	I <sub>OH</sub> = -16mA	2.1/	2.4				
		I <sub>OH</sub> = -24mA	3 V	2.3				
		I <sub>OH</sub> = -32mA	4.5 V	3.8				
		I <sub>OL</sub> = 100μA	1.4 V to 5.5V			0.1		
		I <sub>OL</sub> = 3mA	1.4 V			.4		
		I <sub>OL</sub> = 4mA	1.65 V			0.45	V	
V <sub>OL</sub>	High-level Input Voltage	I <sub>OL</sub> = 8mA	2.3V			0.3		
		I <sub>OL</sub> = 16mA	2.1/			0.4		
		I <sub>OL</sub> = 24mA	3 V			0.55		
		I <sub>OL</sub> = 32mA	4.5			0.55		
I <sub>I</sub>	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μA	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1 \text{ or } V_0 = 5.5 V$	0			± 10	μA	
I <sub>CC</sub>	Supply Current	$V_1 = 5.5V \text{ of GND}$ $I_0=0$	1.4 V to 5.5V			10	μA	
ΔI <sub>CC</sub>	Additional Supply Current	One input at $V_{CC}$ – 0.6 V Other inputs at $V_{CC}$ or GND	3 V to 5.5V			500	μA	
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF	
		SOT25	(Note 5)		204			
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W	
		DFN1410	(Note 5)		430		7	
		SOT25	(Note 5)		52			
θ <sub>JC</sub>	Thermal Resistance	SOT353	(Note 5)		143		°C/W	
	Junction-to-Case	DFN1410	(Note 5)		190			

Over recommended free-air temperature range (unless otherwise noted)

Note: 5. Test condition for SOT25, SOT353, and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



## SINGLE 2 INPUT POSITIVE NAND GATE

### **Switching Characteristics**

Parameter	From	то	± 0.1V				Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit		
T arameter	(Input)	nput) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Мах	Min	Мах	•
t <sub>pd</sub>	A or B	Y	2.2	7.2	1.5	5	0.6	3.5	0.6	3.1	0.7	3	ns

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From TO		Vcc = ± 0			: 1.8 V .15V		: 2.5 V ).2V		: 3.3 V ).3V	Vcc ± 0	= 5 V ).5V	Unit
i arameter	(Input)	(Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	•
t <sub>pd</sub>	A or B	Y	3.1	9	2.1	6.3	1	4.4	0.8	3.8	0.9	3.6	ns

### **Operating Characteristics**

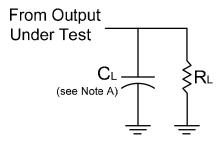
#### $T_A = 25 \ ^{o}C$

Р	arameter	Test	Vcc = 1.5 V	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit
		Conditions	TYP	TYP	ТҮР	ТҮР	ТҮР	
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	22	22	22	23	25	pF

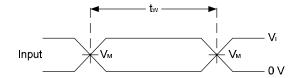


## SINGLE 2 INPUT POSITIVE NAND GATE

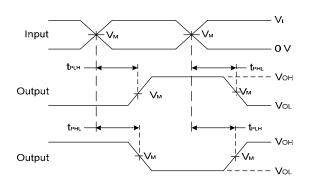
#### **Parameter Measurement Information**



Vcc	In	puts	Ver	C	Р.	
VCC	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	RL	
1.5V±0.10V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ	
1.8V±0.15V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ	
2.5V±0.2V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ	
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ	
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	15pF	1MΩ	



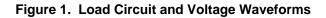
Voltage Waveform Pulse Duration



#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A. Includes test lead and test apparatus capacitance.

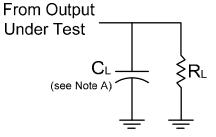
- B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{\mathsf{PLH}}$  and  $t_{\mathsf{PHL}}$  are the same as  $t_{\mathsf{PD}}$



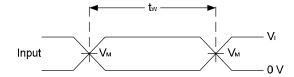


## SINGLE 2 INPUT POSITIVE NAND GATE

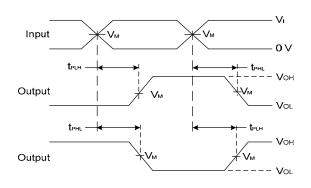
### Parameter Measurement Information (Continued)



Vcc	Inp	outs	V <sub>M</sub>	CL	RL	
	Vı	t <sub>r</sub> /t <sub>f</sub>	- 101	°L		
1.5V±0.10V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1KΩ	
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1KΩ	
2.5V±0.2V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω	



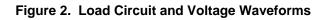
Voltage Waveform Pulse Duration



#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Notes: A. Includes test lead and test apparatus capacitance.

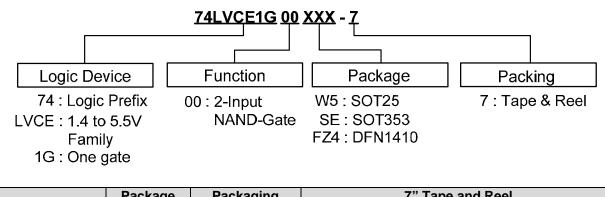
- B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$





## SINGLE 2 INPUT POSITIVE NAND GATE

### **Ordering Information**



	Device	Package Packaging		7" Tape and Reel		
	Device	Code	(Note 5)	Quantity	Part Number Suffix	
<b>Pb</b> ,	74LVCE1G00W5-7	W6	SOT25	3000/Tape & Reel	-7	
<b>Pb</b>	74LVCE1G00SE-7	SE	SOT353	3000/Tape & Reel	-7	
<b>P</b>	74LVCE1G00FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7	

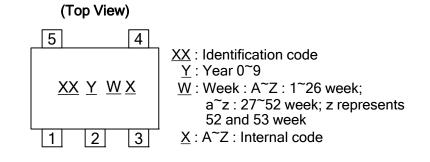
Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



### SINGLE 2 INPUT POSITIVE NAND GATE

#### **Marking Information**

#### (1) SOT25 and SOT353



Part Number	Package	Identification Code
74LVCE1G00W5	SOT25	PS
74LVCE1G00SE	SOT353	PS

(3) DFN1410

### (Top View)

 $\underbrace{XX}_{\underline{Y}} : \text{Identification Code} \\ \underline{Y} : \text{Year} : 0 \sim 9 \\ \underline{W} : \text{Week} : A \sim Z : 1 \sim 26 \text{ week}; \\ a \sim z : 27 \sim 52 \text{ week}; z \text{ represents} \\ 52 \text{ and } 53 \text{ week} \\ \underline{X} : A \sim Z : \text{Internal code} \end{aligned}$ 

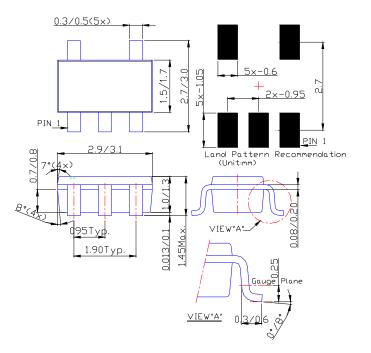
Part Number	Package	Identification Code
74LVCE1G00FZ4	DFN1410	PS



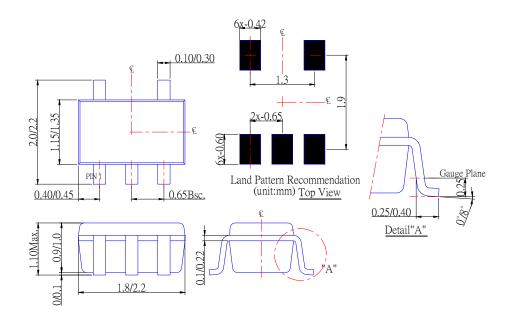
## SINGLE 2 INPUT POSITIVE NAND GATE

### Package Outline Dimensions (All Dimensions in mm)

#### (1) Package Type: SOT25



#### (2) Package Type: SOT353



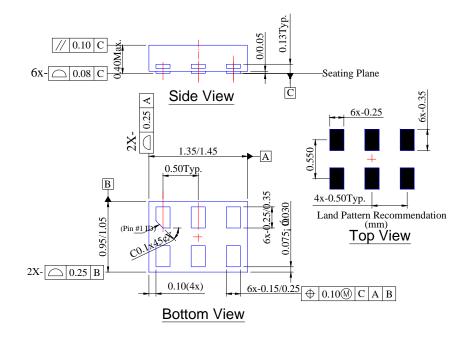
NEW PRODUCT



## SINGLE 2 INPUT POSITIVE NAND GATE

## Package Outline Dimensions (Continued)

#### (3) Package Type: DFN1410

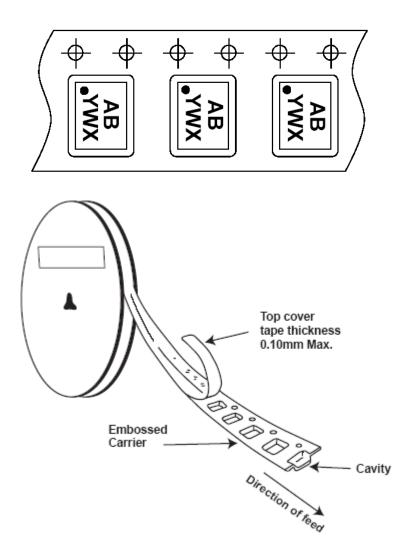


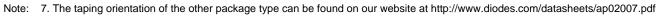


## SINGLE 2 INPUT POSITIVE NAND GATE

### **Taping Orientation (Note 7)**

#### For DFN1410







### SINGLE 2 INPUT POSITIVE NAND GATE

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